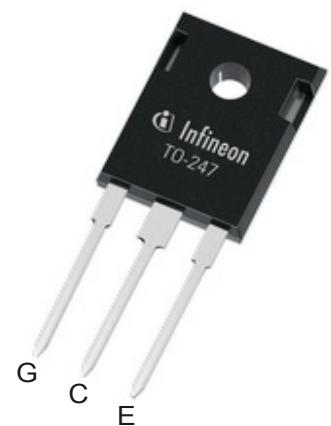
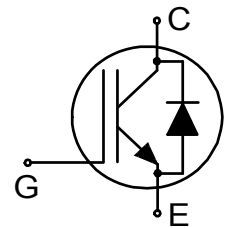


TRENCHSTOP™ Series

Low Loss DuoPack: IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery antiparallel Emitter Controlled diode

Features:

- Automotive AEC-Q101 qualified
- Designed for DC/AC converters for Automotive Application
- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum junction temperature 175°C
- Dynamically stress tested
- Short circuit withstand time 5μs
- 100% short circuit tested
- 100% of the parts are dynamically tested
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low gate charge Q_G
- Green package
- Very soft, fast recovery antiparallel Emitter Controlled HE diode
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers:
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - very high switching speed



Applications:

- Main inverter
- Climate compressor
- PTC heater
- Motor drives



Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat} , $T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
AIKW20N60CT	600V	20A	1.5V	175°C	AK20DCT	PG-TO247-3



TRENCHSTOP™ Series

Table of Contents

Description 1

Table of Contents 2

Maximum Ratings 3

Thermal Resistance 3

Electrical Characteristics 4

Electrical Characteristics Diagrams 6

Package Drawing13

Testing Conditions14

Revision History15

Disclaimer16

TRENCHSTOP™ Series

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_C	40.0 20.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	60.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	60.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	I_F	40.0 20.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	60.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$	t_{SC}	5	μs
Power dissipation $T_C = 25^{\circ}\text{C}$	P_{tot}	166.0	W
Operating junction temperature	T_{vj}	$-40 \dots +175$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55 \dots +150$	$^{\circ}\text{C}$
Soldering temperature, ¹⁾ wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, ²⁾ junction - case	R _{th(j-c)}		-	-	0.90	K/W
Diode thermal resistance, ²⁾ junction - case	R _{th(j-c)}		-	-	1.50	K/W
Thermal resistance junction - ambient	R _{th(j-a)}		-	-	40	K/W

¹⁾ Package not recommended for surface mount application

²⁾ Thermal resistance of thermal grease $R_{th(c-s)}$ (case to heat sink) of more than 0.1K/W not included.

TRENCHSTOP™ Series

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	600	-	-	V
Collector-emitter saturation voltage	V_{CESat}	$V_{GE} = 15.0V, I_C = 20.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.50 1.90	2.05 -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 20.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.65 1.60	2.05 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.29mA, V_{CE} = V_{GE}$	4.1	4.9	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- 550	40 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 20.0A$	-	11.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	1100	-	pF
Output capacitance	C_{oes}		-	71	-	
Reverse transfer capacitance	C_{res}		-	32	-	
Gate charge	Q_G	$V_{CC} = 480V, I_C = 20.0A, V_{GE} = 15V$	-	120.0	-	nC
Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0s$	$I_{C(SC)}$	$V_{GE} = 15.0V, V_{CC} \leq 400V, t_{SC} \leq 5\mu s, T_{vj} = 150^{\circ}C$	-	183	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(\text{on})} = 12.0\Omega, R_{G(\text{off})} = 12.0\Omega,$ $L\sigma = 131\text{nH}, C\sigma = 31\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	199	-	ns
Fall time	t_f		-	42	-	ns
Turn-on energy	E_{on}		-	0.31	-	mJ
Turn-off energy	E_{off}		-	0.46	-	mJ
Total switching energy	E_{ts}		-	0.77	-	mJ

TRENCHSTOP™ Series

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 20.0\text{A},$ $di_F/dt = 880\text{A}/\mu\text{s}$	-	41	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.31	-	μC
Diode peak reverse recovery current	I_{rrm}		-	13.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-711	-	$\text{A}/\mu\text{s}$

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 175^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega,$ $L\sigma = 131\text{nH}, C\sigma = 31\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	18	-	ns
Turn-off delay time	$t_{d(off)}$		-	223	-	ns
Fall time	t_f		-	76	-	ns
Turn-on energy	E_{on}		-	0.51	-	mJ
Turn-off energy	E_{off}		-	0.64	-	mJ
Total switching energy	E_{ts}		-	1.15	-	mJ

Diode Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 175^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 20.0\text{A},$ $di_F/dt = 880\text{A}/\mu\text{s}$	-	176	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.46	-	μC
Diode peak reverse recovery current	I_{rrm}		-	18.9	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-467	-	$\text{A}/\mu\text{s}$

TRENCHSTOP™ Series

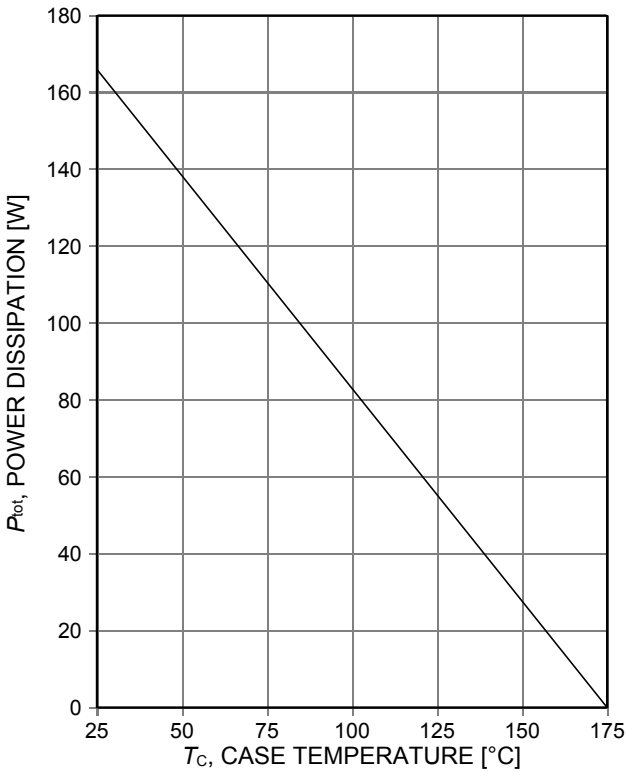


Figure 1. **Power dissipation as a function of case temperature**
($T_J \leq 175^\circ\text{C}$)

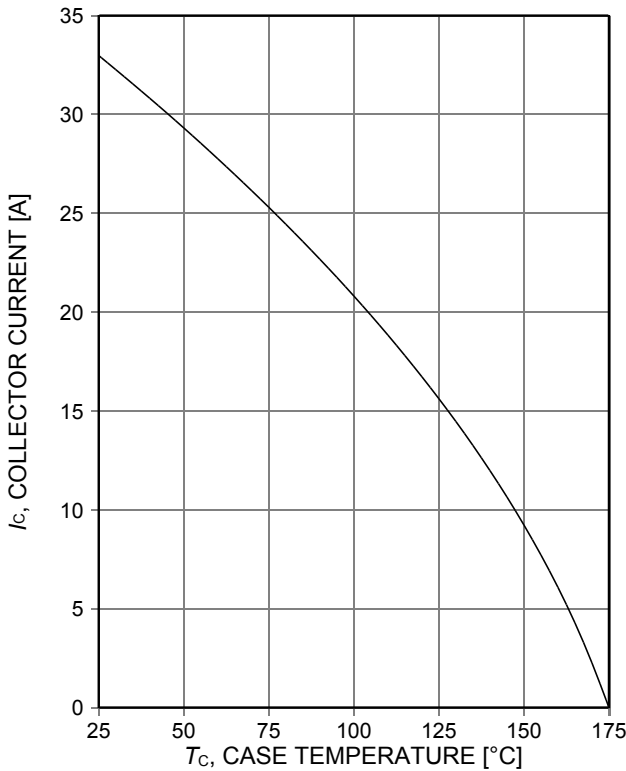


Figure 2. **Collector current as a function of case temperature**
($V_{GE} \geq 15\text{V}$, $T_J \leq 175^\circ\text{C}$)

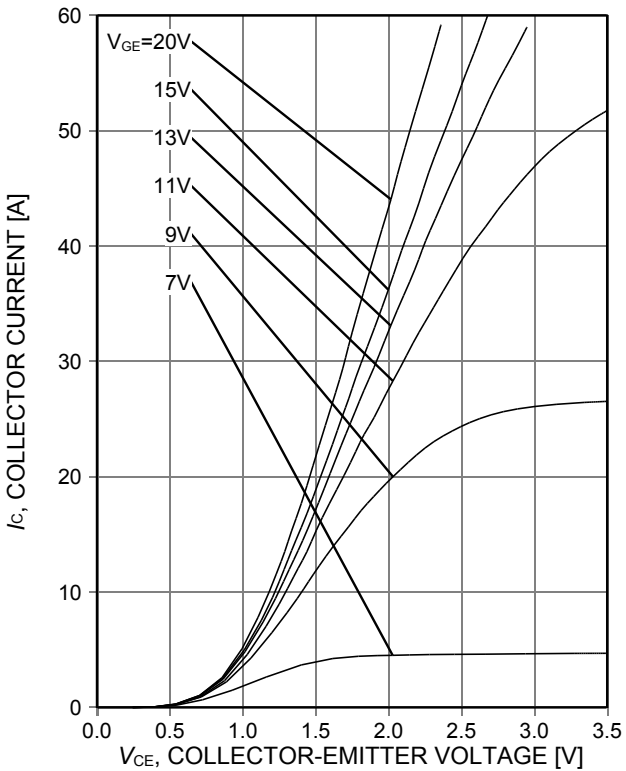


Figure 3. **Typical output characteristic**
($T_J = 25^\circ\text{C}$)

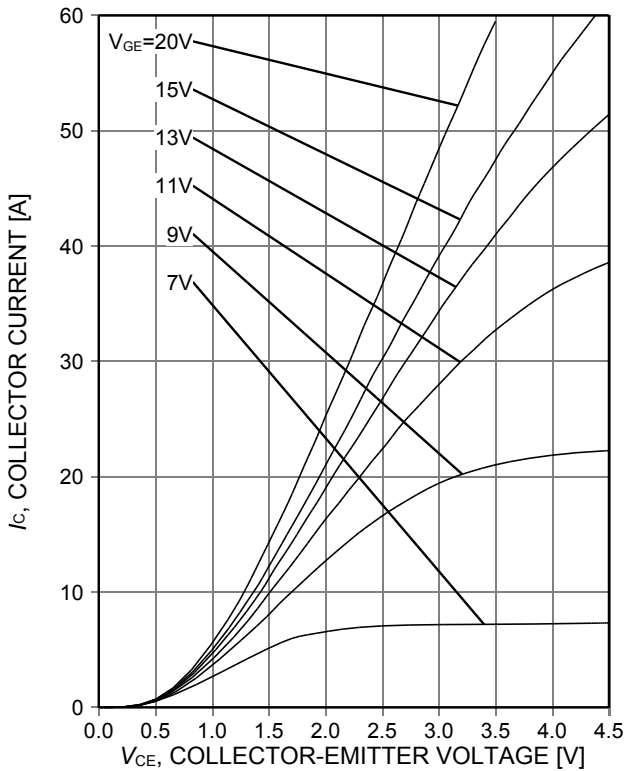


Figure 4. **Typical output characteristic**
($T_J = 175^\circ\text{C}$)

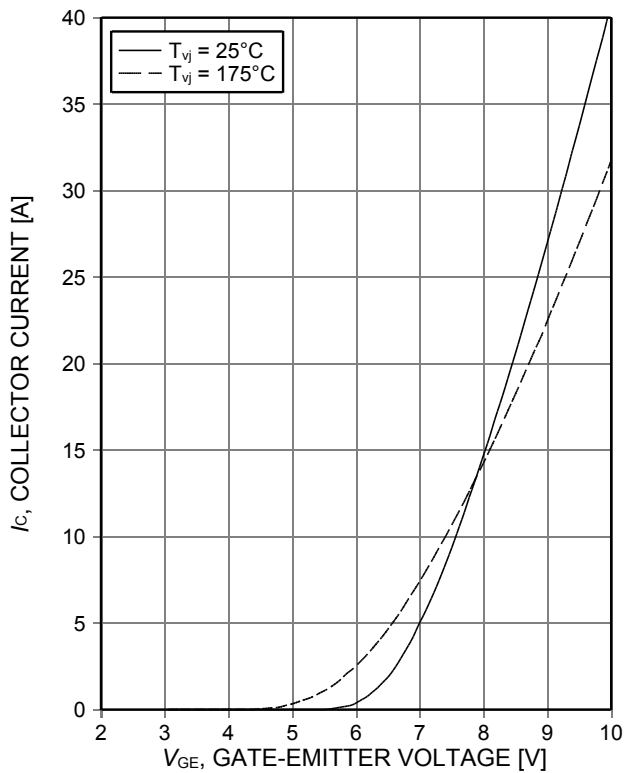


Figure 5. **Typical transfer characteristic**
($V_{CE}=20V$)

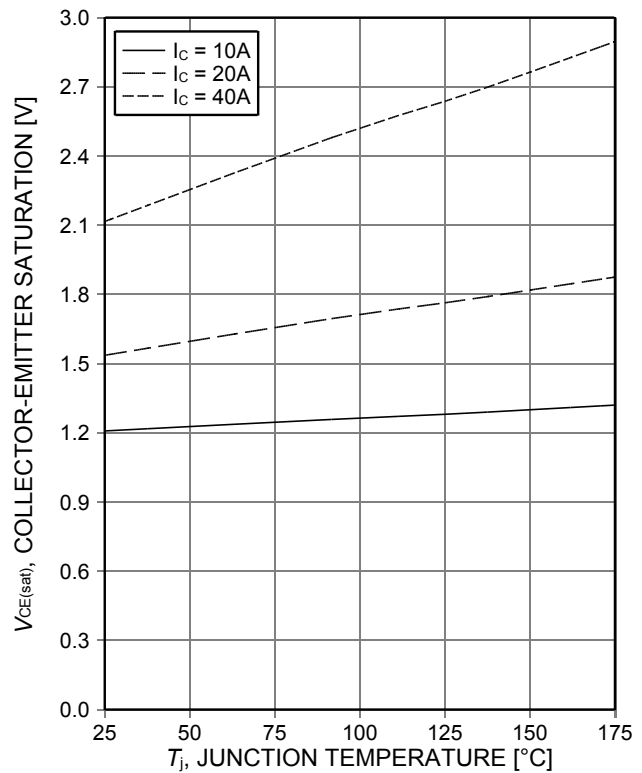


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15V$)

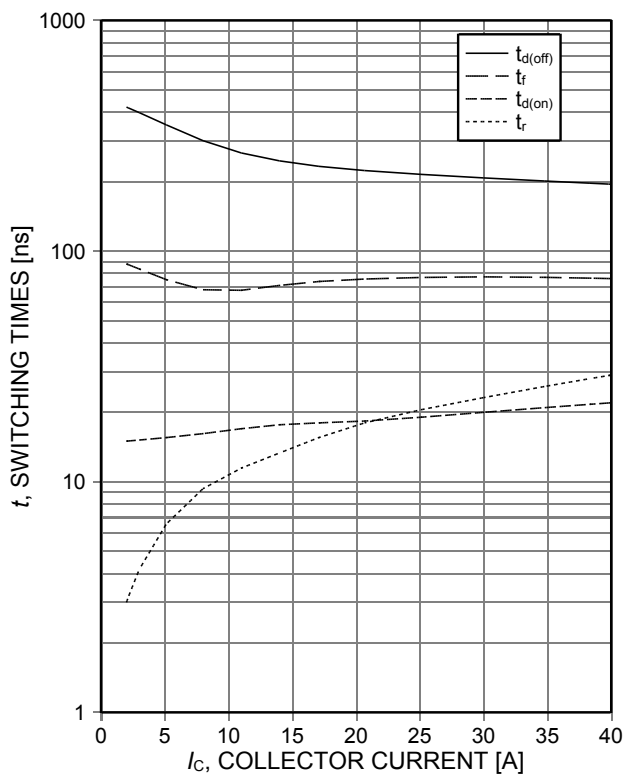


Figure 7. **Typical switching times as a function of collector current**
(inductive load, $T_j=175^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

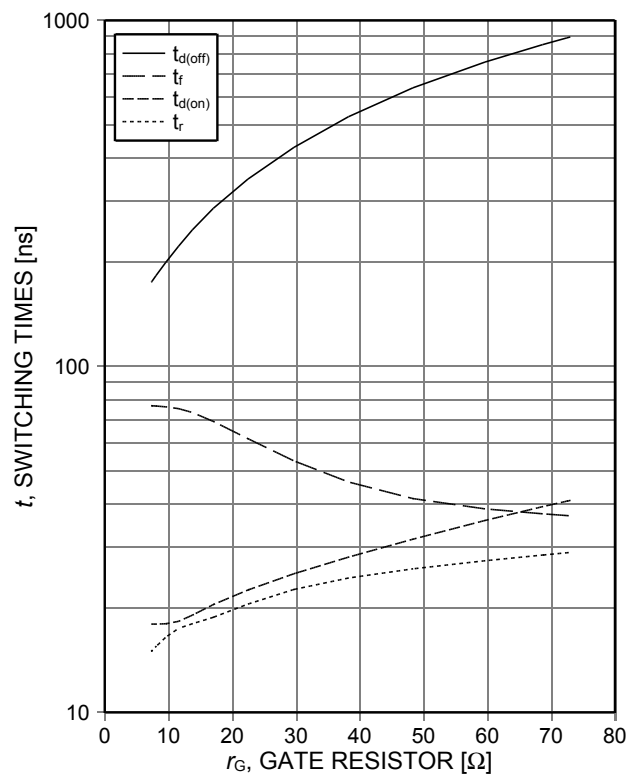


Figure 8. **Typical switching times as a function of gate resistor**
(inductive load, $T_j=175^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=20A$, Dynamic test circuit in Figure E)

TRENCHSTOP™ Series

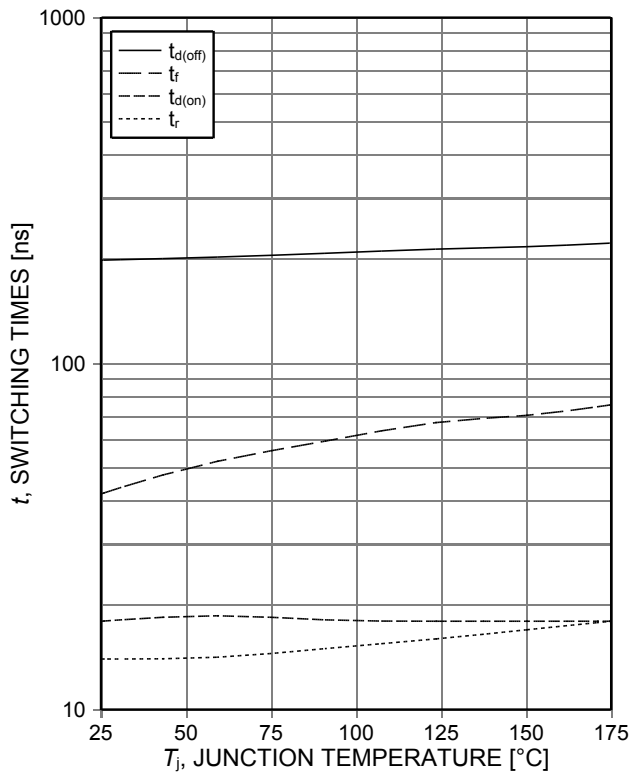


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=20A$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

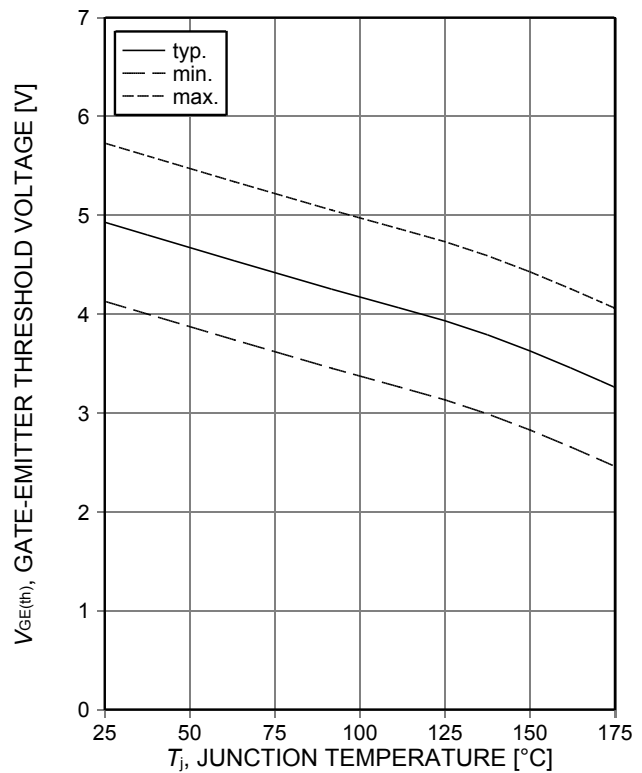


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0,29mA$)

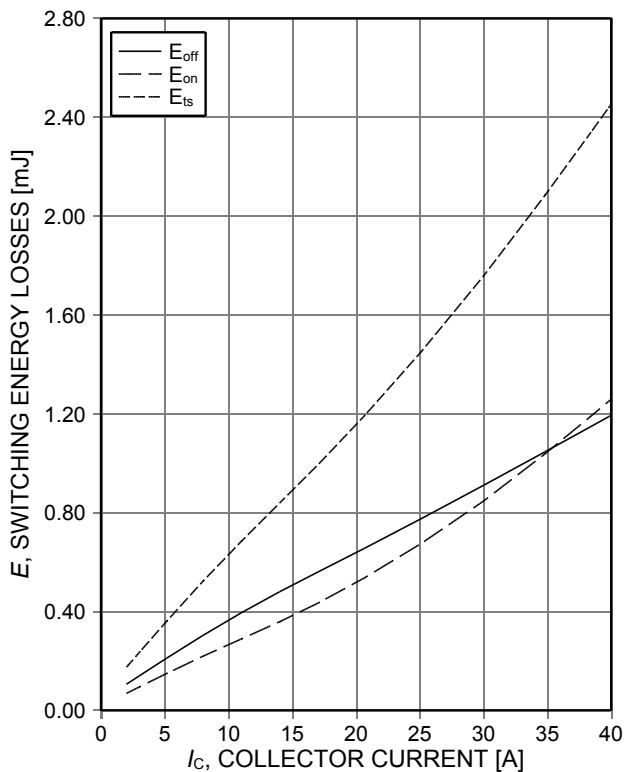


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, $T_j=175^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

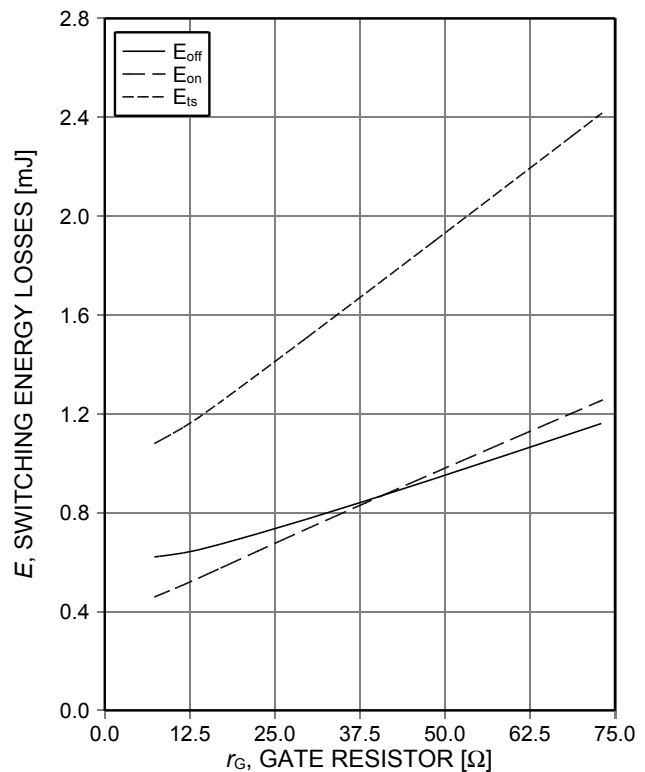


Figure 12. **Typical switching energy losses as a function of gate resistor**
(inductive load, $T_j=175^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=20A$, Dynamic test circuit in Figure E)

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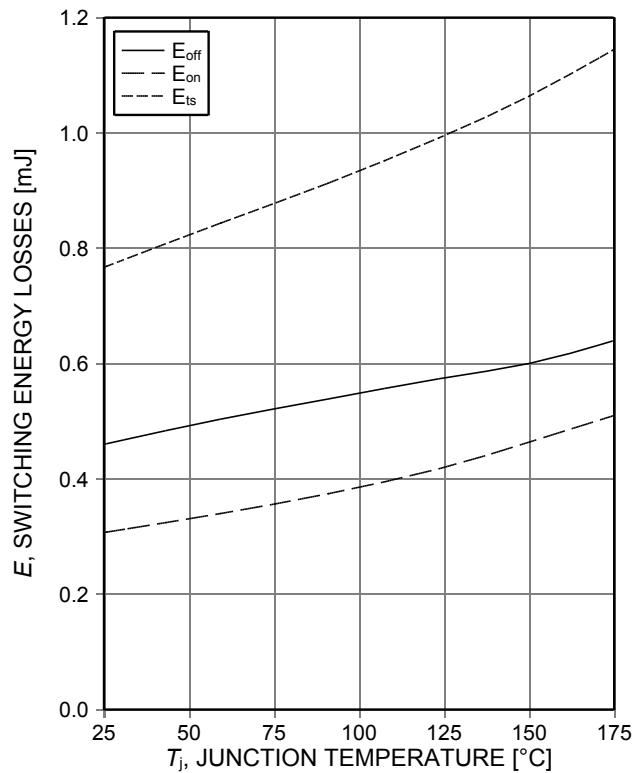


Figure 13. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=20A$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

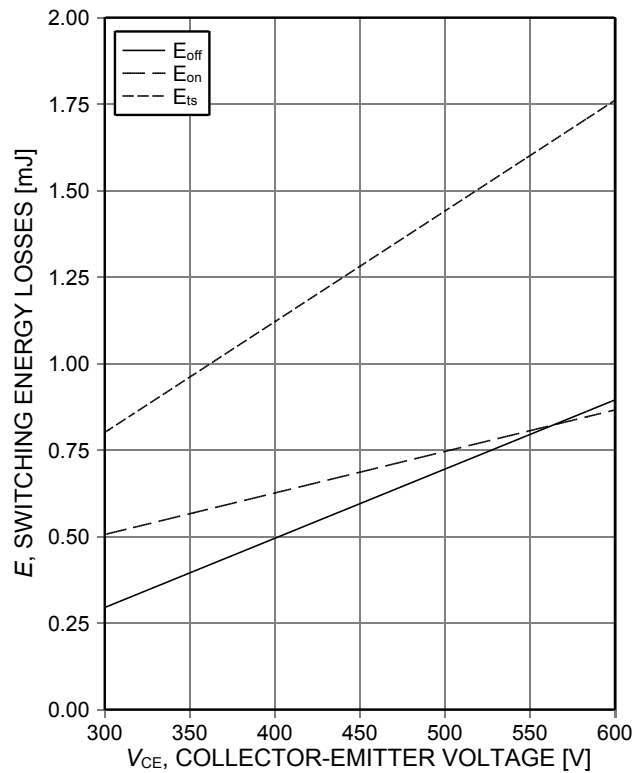


Figure 14. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, $T_J=175^\circ C$, $V_{GE}=0/15V$, $I_C=20A$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

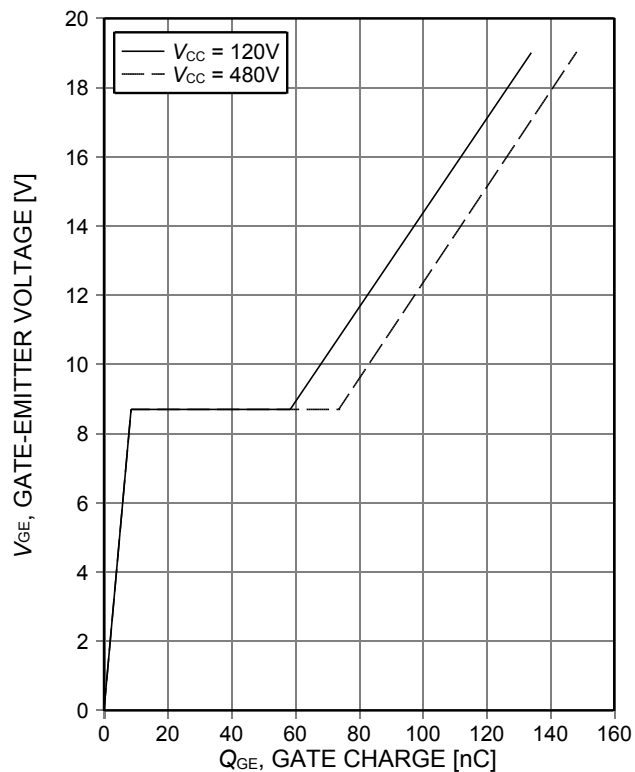


Figure 15. **Typical gate charge**
($I_C=20A$)

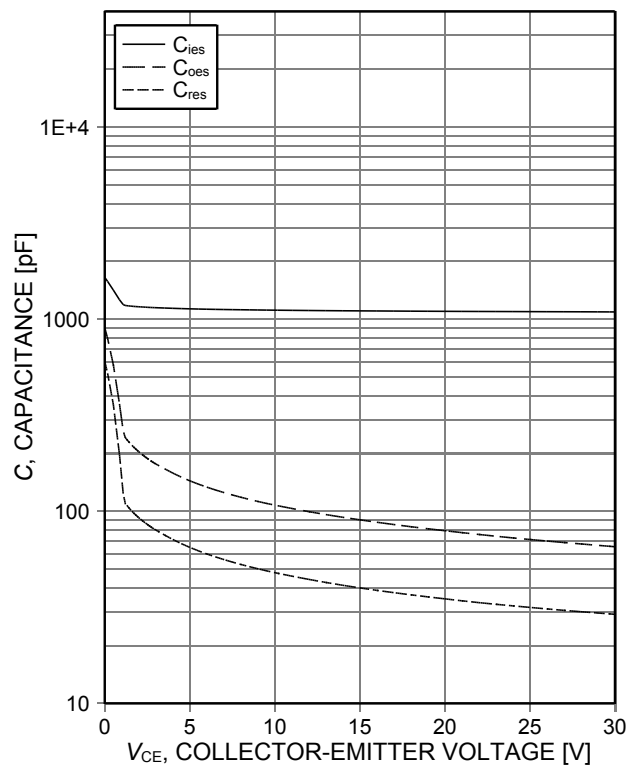


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

TRENCHSTOP™ Series

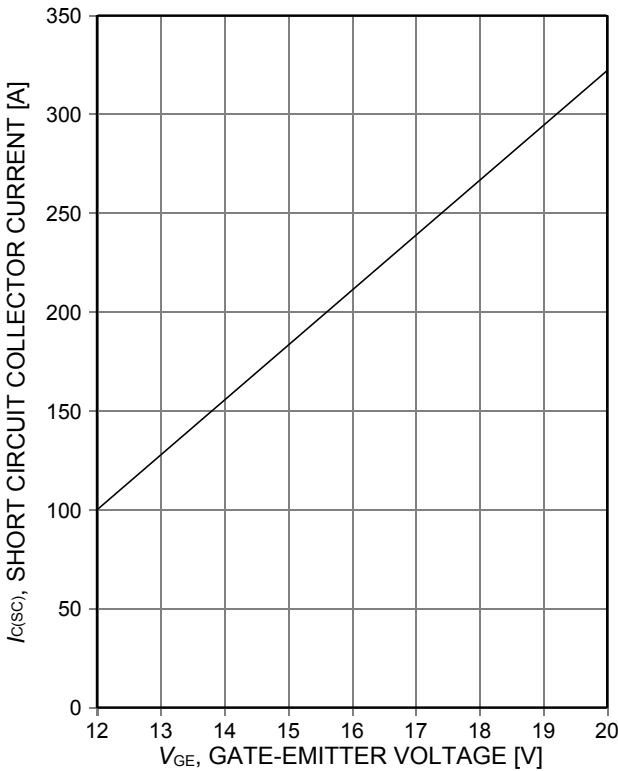


Figure 17. **Typical short circuit collector current as a function of gate-emitter voltage**
($V_{CE} \leq 400V$, start at $T_J \leq 150^\circ C$)

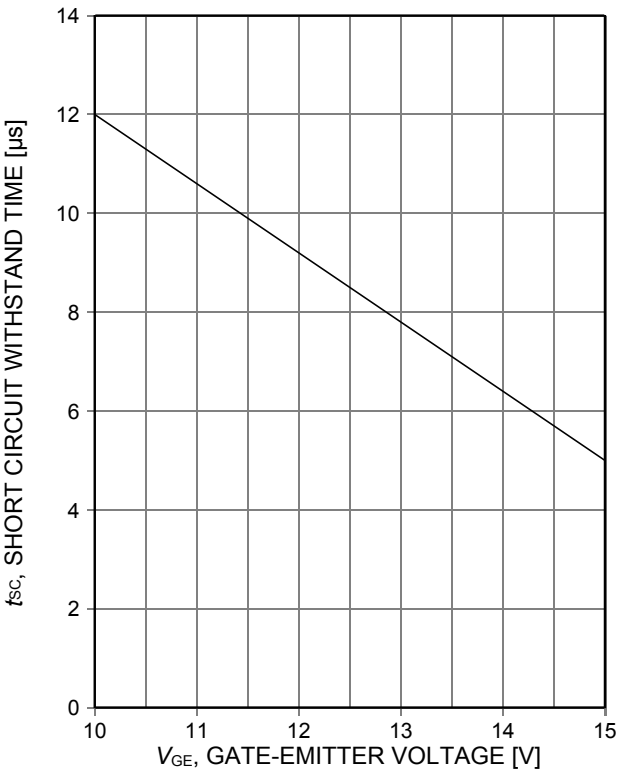


Figure 18. **Short circuit withstand time as a function of gate-emitter voltage**
($V_{CE} = 400V$, start at $T_J = 25^\circ C$, $T_{Jmax} \leq 150^\circ C$)

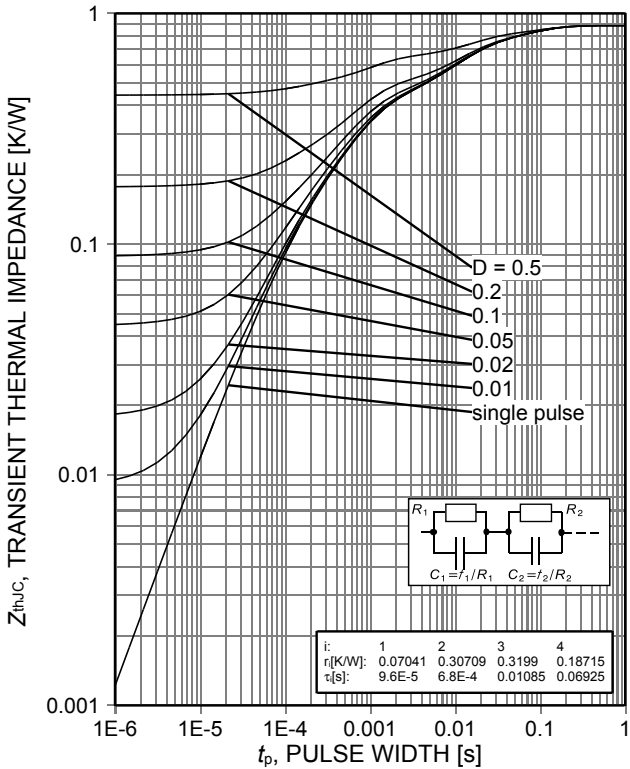


Figure 19. **IGBT transient thermal impedance as a function of pulse width for different duty cycles D**
($D = t_p/T$)

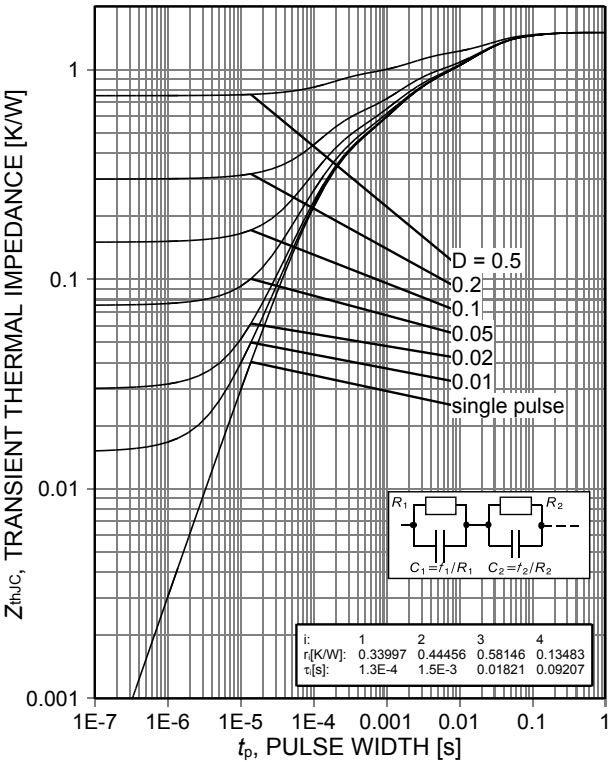


Figure 20. **Diode transient thermal impedance as a function of pulse width for different duty cycles D**
($D = t_p/T$)

TRENCHSTOP™ Series

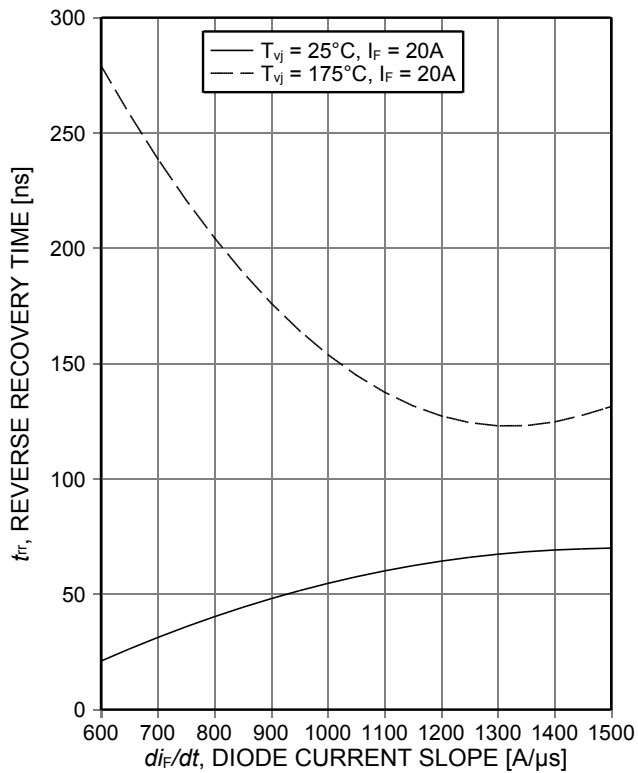


Figure 21. **Typical reverse recovery time as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

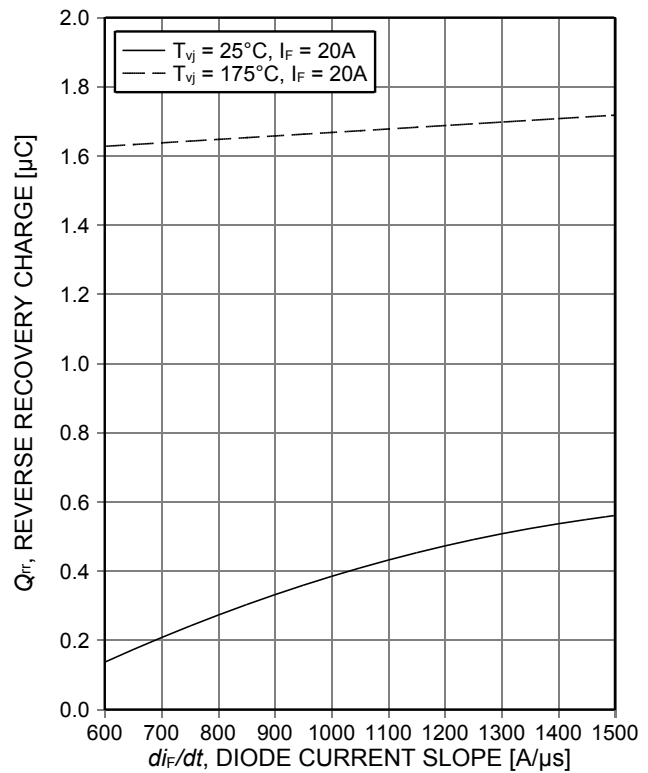


Figure 22. **Typical reverse recovery charge as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

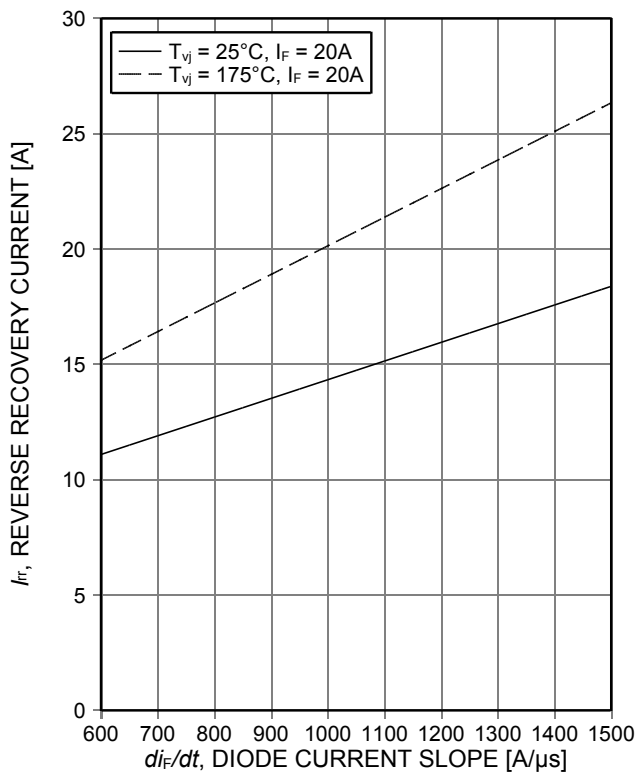


Figure 23. **Typical reverse recovery current as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

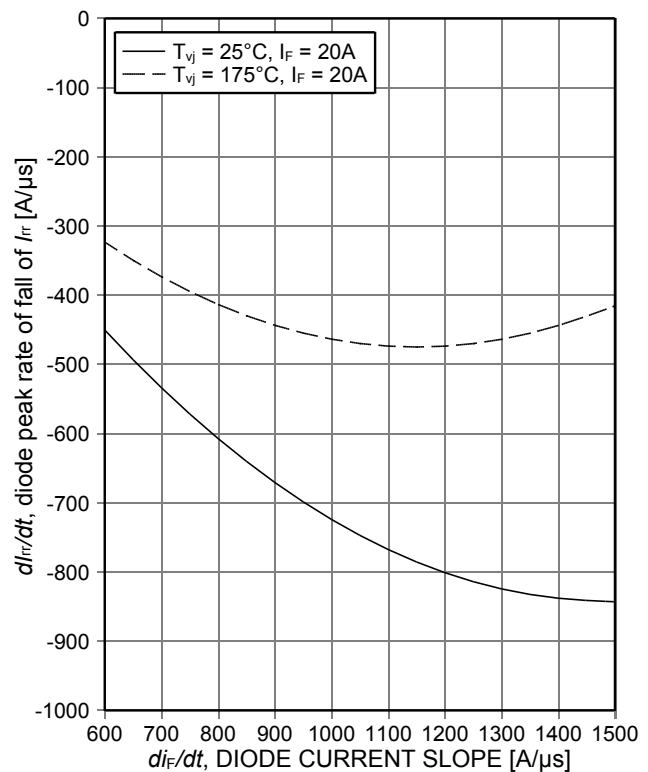


Figure 24. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

TRENCHSTOP™ Series

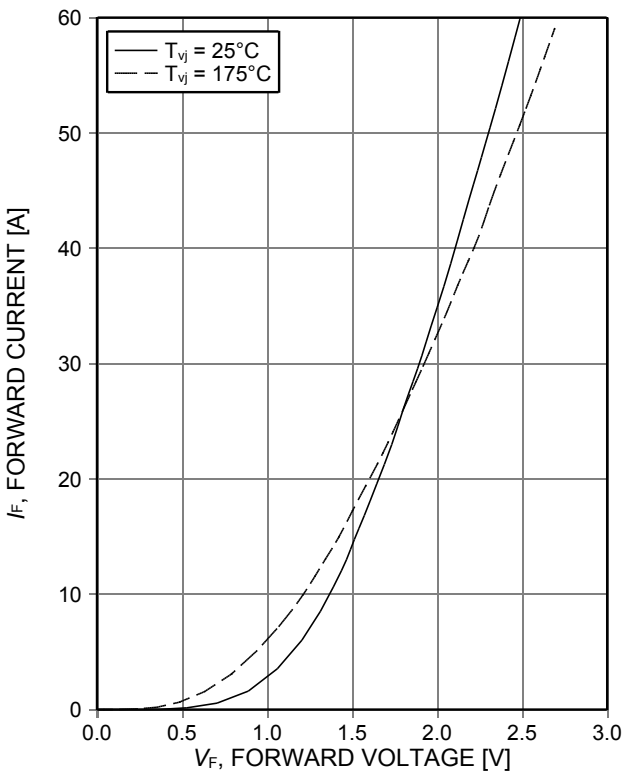


Figure 25. Typical diode forward current as a function of forward voltage

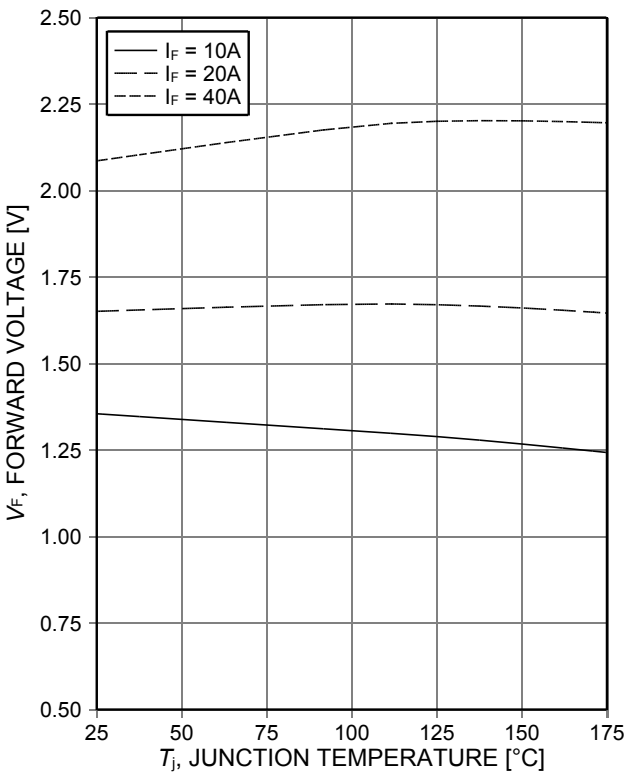
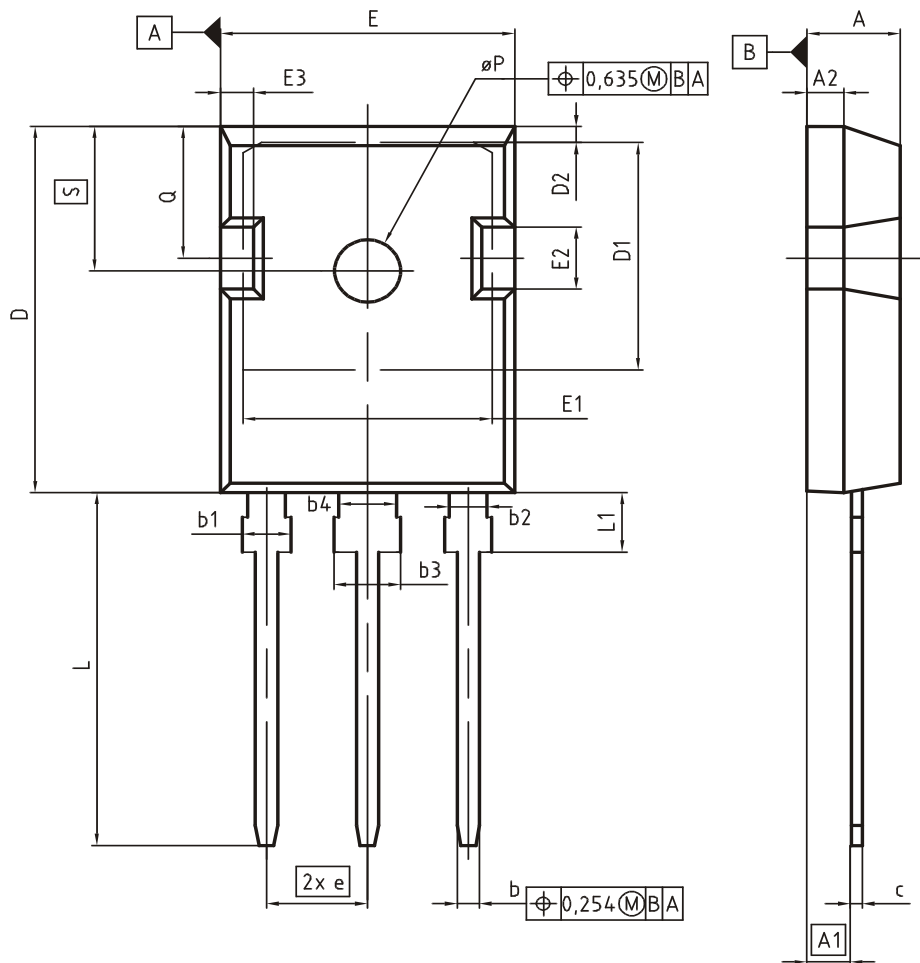
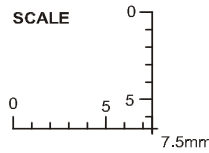
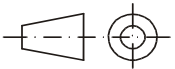


Figure 26. Typical diode forward voltage as a function of junction temperature

Package Drawing PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
ØP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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REVISION 05

Testing Conditions

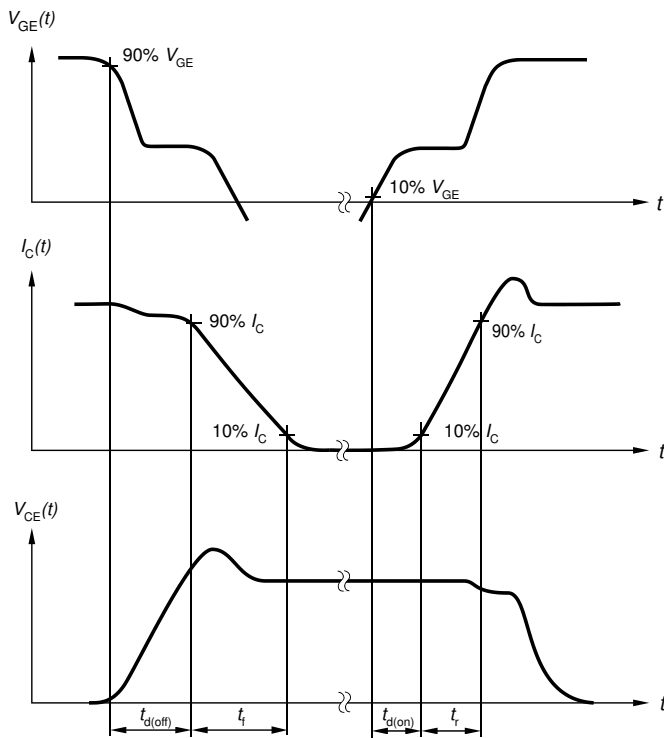


Figure A. Definition of switching times

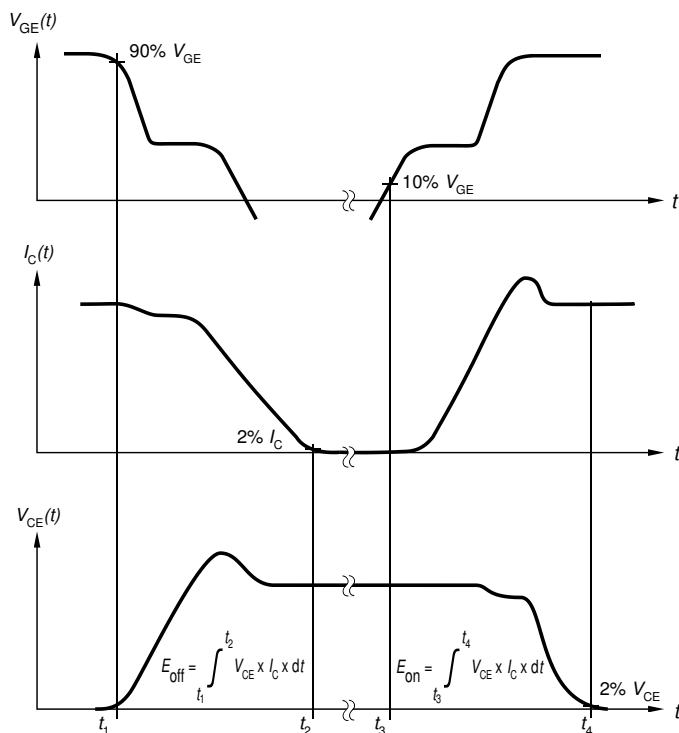


Figure B. Definition of switching losses

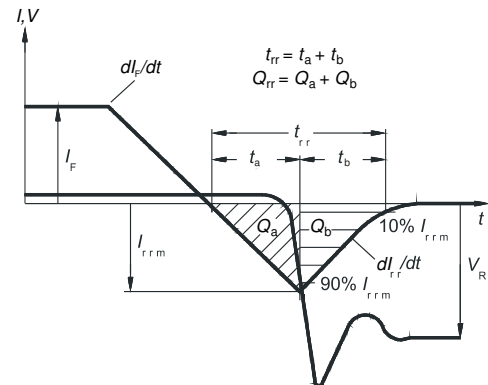


Figure C. Definition of diode switching characteristics

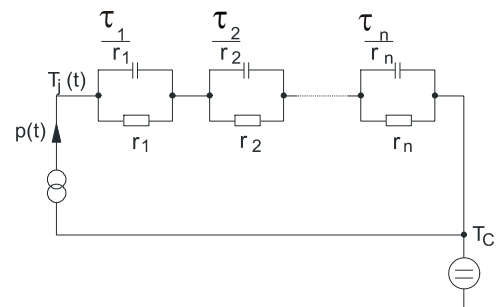


Figure D. Thermal equivalent circuit

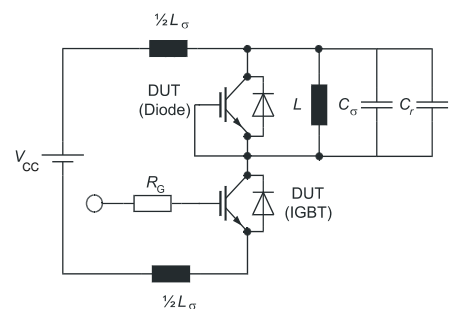


Figure E. **Dynamic test circuit**
 Parasitic inductance L_σ ,
 parasitic capacitor C_σ ,
 relief capacitor C_r ,
 (only for ZVT switching)

Revision History

AIKW20N60CT

Revision: 2017-02-09, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2017-02-09	Data sheet created

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